



QUAD 2-INPUT OPEN DRAIN NAND GATE

- HIGH SPEED: $t_{PD} = 3.7 \text{ ns}$ (TYP.) at $V_{CC} = 5V$
- LOW POWER DISSIPATION:
 $I_{CC} = 2 \mu\text{A}$ (MAX.) at $T_A = 25 \text{ }^\circ\text{C}$
- HIGH NOISE IMMUNITY:
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (MIN.)
- POWER DOWN PROTECTION ON INPUTS
- OPERATING VOLTAGE RANGE:
 $V_{CC} \text{ (OPR)} = 2V \text{ to } 5.5V$
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 03
- IMPROVED LATCH-UP IMMUNITY
- LOW NOISE: $V_{OLP} = 0.8V$ (Max.)

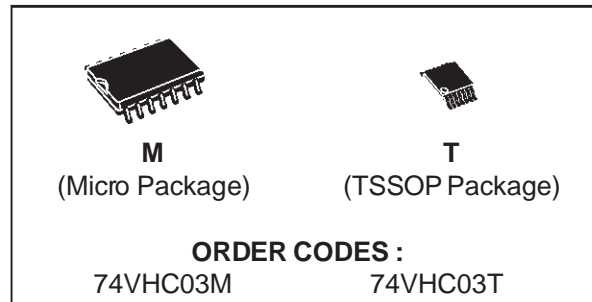
DESCRIPTION

The 74VHC03 is an advanced high-speed CMOS QUAD 2-INPUT OPEN DRAIN NAND GATE fabricated with sub-micron silicon gate and double-layer metal wiring C^2 MOS technology.

The internal circuit is composed of 3 stages including buffer output, which provides high noise immunity and stable output.

This device can, with an external pull-up resistor,

PRELIMINARY DATA

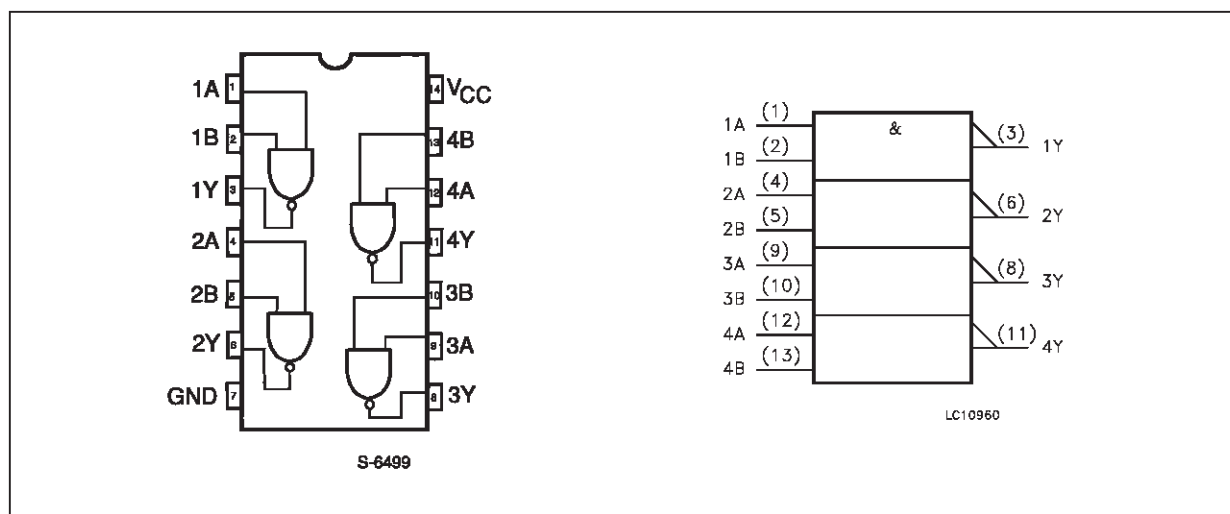


be used in wired AND configuration. This device can also be used as a led driver and in any other application requiring a current sink.

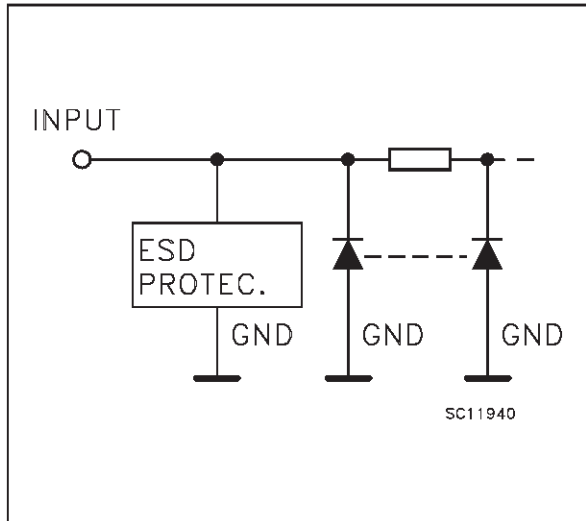
Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2kV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 9, 12	1A to 4A	Data Inputs
2, 5, 10, 13	1B to 4B	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	B	Y
L	L	Z
L	H	Z
H	L	Z
H	H	L

Z: High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2.0 to 5.5	V
V _I	Input Voltage	0 to 5.5	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-40 to +85	°C
dt/dv	Input Rise and Fall Time (see note 1) (V _{CC} = 3.3 ± 0.3V) (V _{CC} = 5.0 ± 0.5V)	0 to 100 0 to 20	ns/V ns/V

1) V_{IN} from 30% to 70% of V_{CC}

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value					Unit
				T _A = 25 °C			-40 to 85 °C		
				Min.	Typ.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		V
		3.0 to 5.5		0.7V _{CC}			0.7V _{CC}		
V _{IL}	Low Level Input Voltage	2.0				0.5		0.5	V
		3.0 to 5.5				0.3V _{CC}		0.3V _{CC}	
V _{OL}	Low Level Output Voltage	2.0	I _O =50 μA		0.0	0.1		0.1	V
		3.0	I _O =50 μA		0.0	0.1		0.1	
		4.5	I _O =50 μA		0.0	0.1		0.1	
		3.0	I _O =4 mA			0.36		0.44	
		4.5	I _O =8 mA			0.36		0.44	
I _{OZ}	High Impedance Output Leakage Current	5.5	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			±0.25		±2.5	μA
I _I	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			±0.1		±1.0	μA
I _{CC}	Quiescent Supply Current	5.5	V _I = V _{CC} or GND			2		20	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3 ns)

Symbol	Parameter	Test Condition			Value					Unit
					T _A = 25 °C			-40 to 85 °C		
					Min.	Typ.	Max.	Min.	Max.	
t _{PZL}	Propagation Delay Time	3.3 ^(*)	15	R _L = 1 KΩ		5.5	7.9	1.0	9.5	ns
		3.3 ^(*)	50	R _L = 1 KΩ		8.0	11.4	1.0	13.0	
		5.0 ^(**)	15	R _L = 1 KΩ		3.7	5.5	1.0	6.5	
		5.0 ^(**)	50	R _L = 1 KΩ		5.2	7.5	1.0	8.5	
t _{PLZ}	Propagation Delay Time	3.3 ^(*)	50	R _L = 1 KΩ		8.0	11.4	1.0	13.0	ns
		5.0 ^(**)	50	R _L = 1 KΩ		5.2	7.5	1.0	8.5	

(*) Voltage range is 3.3V ± 0.3V

(**) Voltage range is 5V ± 0.5V

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value					Unit
				T _A = 25 °C			-40 to 85 °C		
				Min.	Typ.	Max.	Min.	Max.	
C _{IN}	Input Capacitance		4	10			10	pF	
C _{OUT}	Output Capacitance		5					pF	
C _{PD}	Power Dissipation Capacitance (note 1)		6					pF	

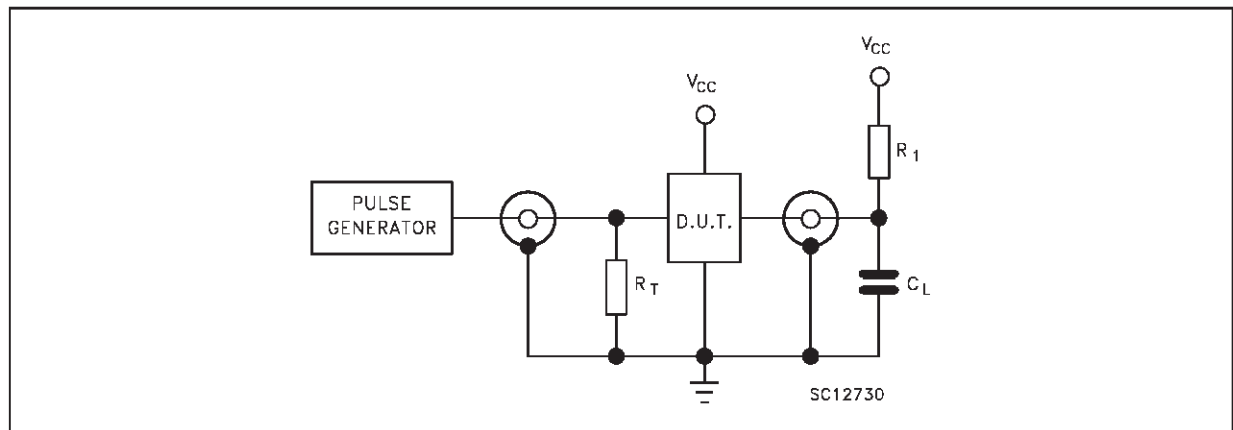
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(oper)} = C_{PD} • V_{CC} • f_{IN} + I_{CC/4} (per Gate)

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value					Unit
				T _A = 25 °C			-40 to 85 °C		
		V _{CC} (V)		Min.	Typ.	Max.	Min.	Max.	
V _{OLP}	Dynamic Low Voltage Quiet Output (note 1, 2)	5.0	C _L = 50 pF		0.3	0.8			V
V _{OLV}				-0.8	-0.3				
V _{IHD}	Dynamic High Voltage Input (note 1, 3)	5.0		3.5					
V _{ILD}	Dynamic Low Voltage Input (note 1, 3)	5.0				1.5			

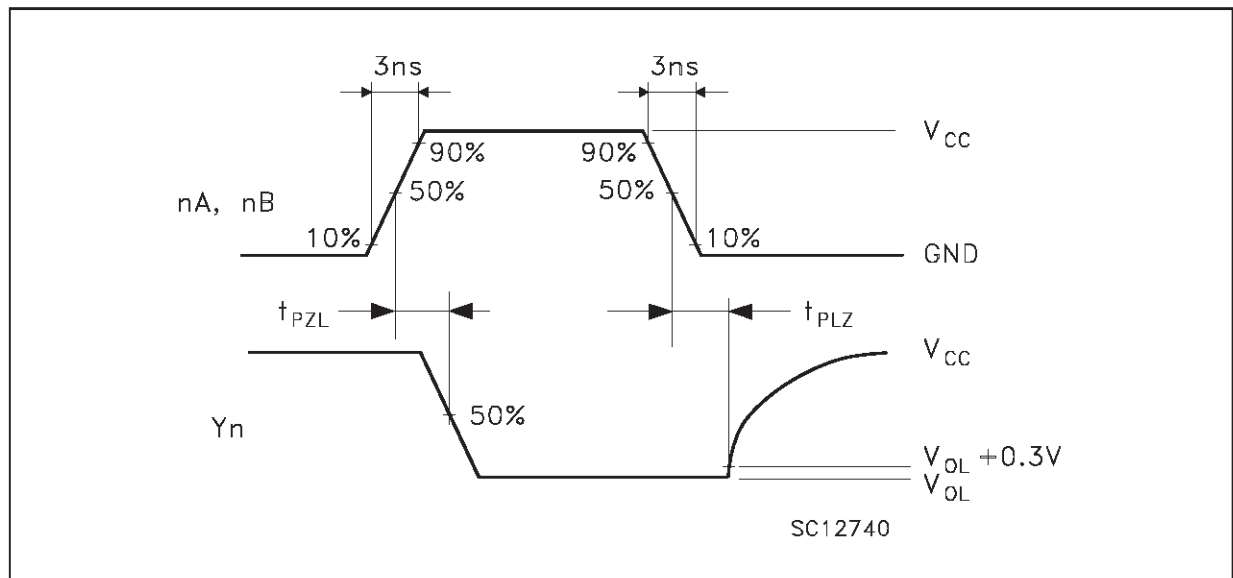
- 1) Worst case package.
- 2) Max number of outputs defined as (n). Data inputs are driven 0V to 5.0V, (n-1) outputs switching and one output at GND.
- 3) Max number of data inputs (n) switching, (n-1) switching 0V to 5.0V. Inputs under test switching: 5.0V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f=1MHz.

TEST CIRCUIT



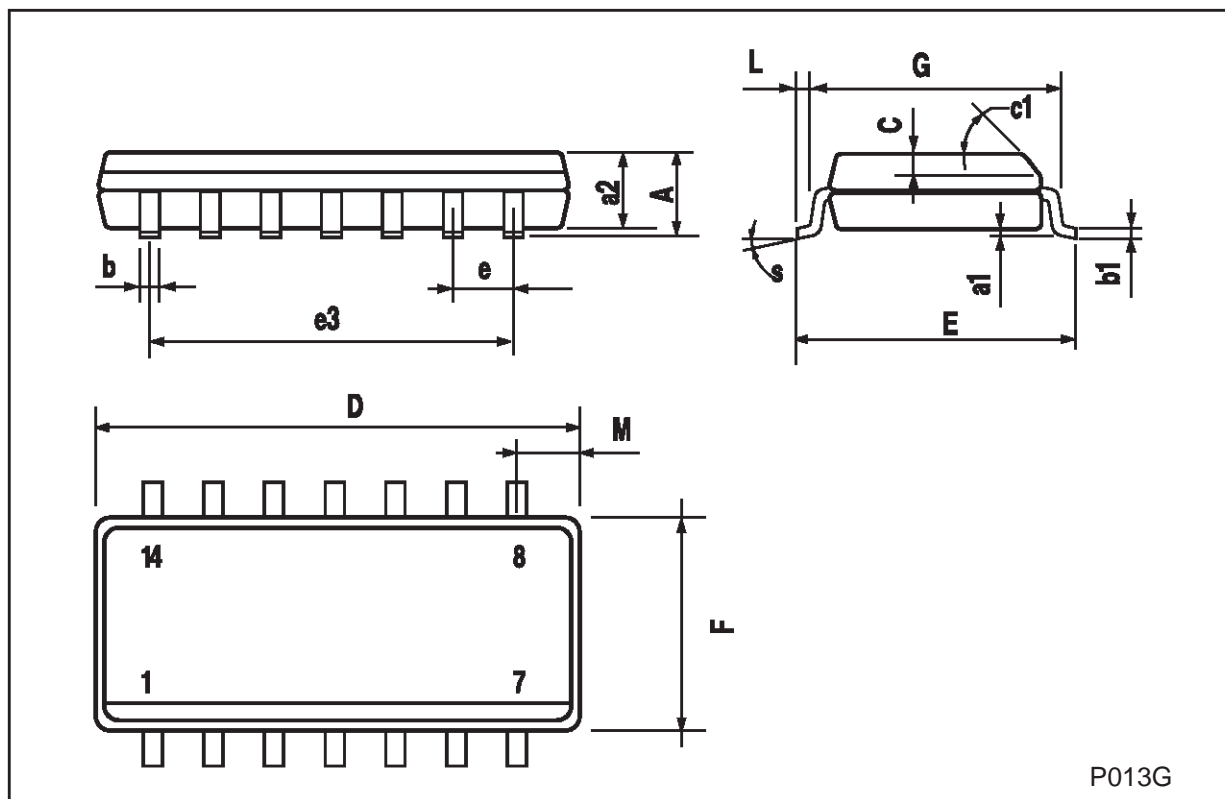
- C_L = 15/50 pF or equivalent (includes jig and probe capacitance)
- R_L = R₁ = 1KΩ or equivalent
- R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)



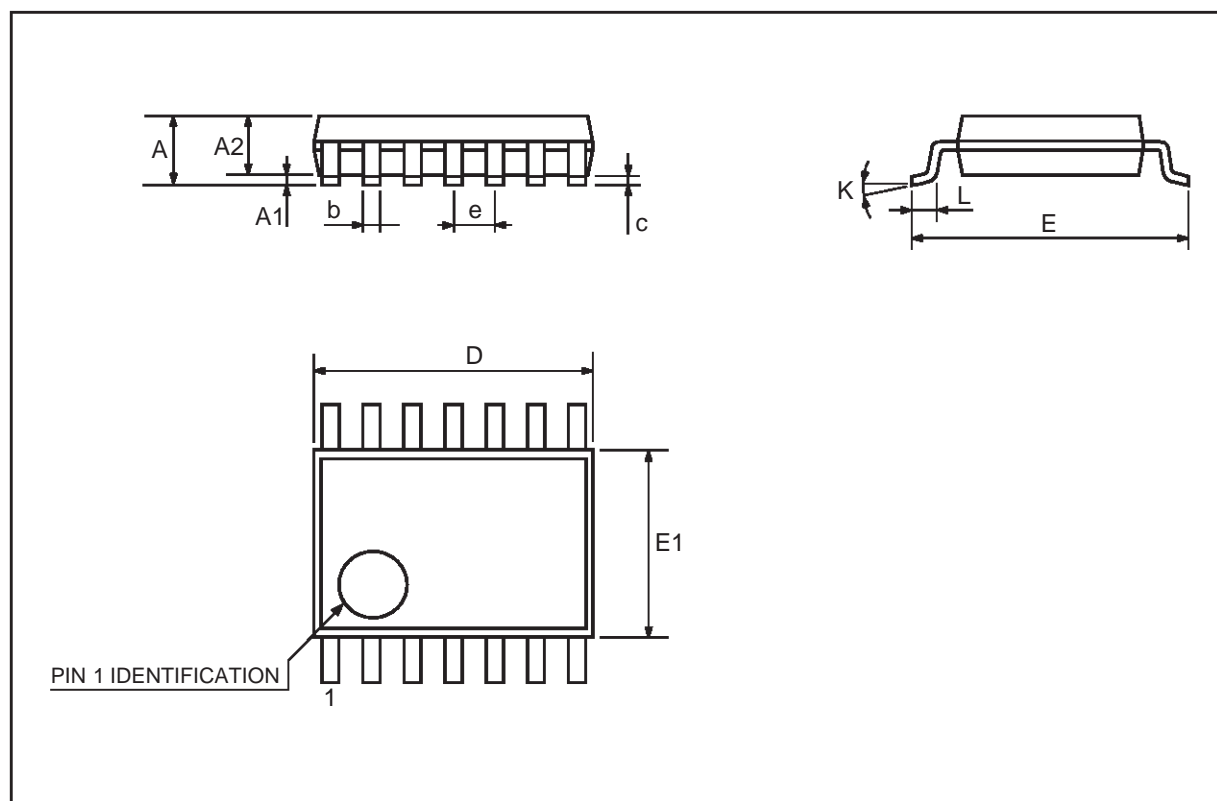
SO-14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45 (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8 (max.)					



TSSOP14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.1			0.433
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.85	0.9	0.95	0.335	0.354	0.374
b	0.19		0.30	0.0075		0.0118
c	0.09		0.20	0.0035		0.0079
D	4.9	5	5.1	0.193	0.197	0.201
E	6.25	6.4	6.5	0.246	0.252	0.256
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°	4°	8°	0°	4°	8°
L	0.50	0.60	0.70	0.020	0.024	0.028



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